
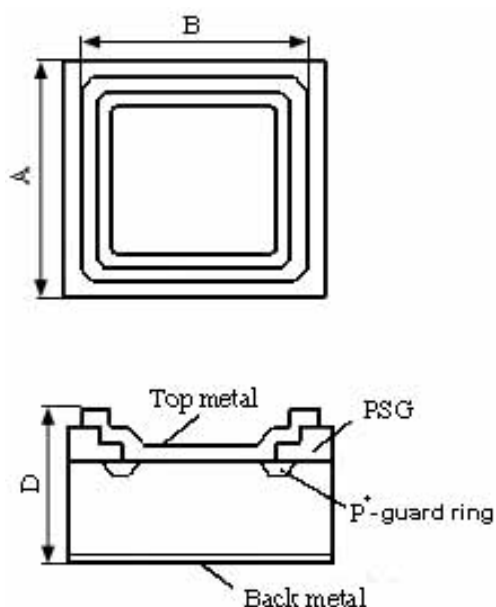


# SCHOTTKY DIODES KDN-40060. PRELIMINARY



Rev.1. Feb. 2010

 <b>VSP-MIKRON</b>	<b>40A/60V. Die Size-150mil.</b>			
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10\text{mA}$	$V_{BR}$	V	60	65
Average Rectified Forward Current	$I_{F(AV)}$	A	40,0	-
DC Forward Voltage @ $25^\circ\text{C}$ , $I_F=40,0\text{A}$ @ $25^\circ\text{C}$ , $I_F=20,0\text{A}$	$V_F$	V	0,67 0,58	0,65 0,56
Maximum Reverse Current  @ $25^\circ\text{C}$ , $V_R=65\text{V}$ $25^\circ\text{C}$ , $V_R=60\text{V}$ $125^\circ\text{C}$ , $V_R=60\text{V}$	$I_R$	mA	- 0,50 350	0,60 0,45 300
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}$	A	400	-
Peak Repetitive Reverse Surge Current @ $2,0\mu\text{s}$ , $f=1\text{kHz}$ ., $T_J<150^\circ\text{C}$ .	$I_{RRM}$	A	5,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	$\pm 8$ (contact)	
Voltage Rate of Change	dV/dt	V/ $\mu\text{S}$	10.000	
Operating Junction Temperature	$T_J$	$^\circ\text{C}$	150	



DIM	ITEM	$\mu\text{m}$
$A_x$ $A_y$	Wafer Form Die Size	3810 3810
$B_x$ $B_y$	Top Metal Size	3670 3670
D	Thickness	350max.
Scribe line Width		80

*Top metal:* a) **Al** – for Wire Bonding;  
b) **Al-Ni-Ag** – for Soldering.  
*Backside metal:* **Ti-Ni-Ag**.